

OCT 25 2004

SHEET 1 OF 23

ATTY DOCKET NO.

248402US99DN

SERIAL NO.

10/767,994

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWP	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Mathews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

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(Modified)U.S. DEPARTMENT OF COMMERCE
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CA		3,766,370	10/16/73	Walther			
CB		4,006,989	02/08/77	Andringa			
CC		4,284,329	08/18/81	Smith et al.			
CD		4,777,613	10/11/98	Shahan et al.			
CE		4,802,182	01/31/89	Thornton et al.			
CF		4,882,300	11/21/89	Inoue et al.			
CG		4,896,194	01/23/90	Suzuki			
CH		4,999,842	03/12/91	Huang et al.			
CI		5,081,062	01/14/92	Vasudev et al.			
CJ		5,155,658	10/13/92	Inam et al.			
CK		5,248,564	09/28/93	Ramesh			
CL		5,260,394	11/09/93	Tazaki et al.			
CM		5,270,298	12/14/93	Ramesh			
CN		5,286,985	02/15/94	Taddiken			
CO		5,310,707	05/10/94	Oishi et al.			
CP		5,326,721	07/05/94	Summerfelt			
CQ		5,404,581	04/04/95	Honjo			
CR		5,418,389	05/23/95	Watanabe			
CS		5,436,759	07/25/95	Dijali et al.			
CT		5,576,879	11/19/96	Nashimoto			
CU		5,606,184	02/25/97	Abrokwah, et al.			
CV		5,640,267	06/17/97	May et al.			
CW		5,674,366	10/07/97	Hayashi et al.			
CX		5,729,641	03/17/98	Chandonnet et al.			
CY		5,790,583	08/04/98	Ho			
CZ		5,825,799	10/20/98	Ho et al.			
DA		5,857,049	01/05/99	Beranek et al.			
DB		5,874,860	02/23/99	Brunel et al.			
DC		5,926,496	07/20/99	Ho et al.			
DD		5,937,285	08/10/99	Abrokwah, et al.			
DE		5,981,400	11/09/99	Lo			
DF		5,990,495	11/23/99	Ohba			
DG		6,002,375	12/14/99	Corman et al.			
DH		6,008,762	12/28/99	Nghiem			
DI		6,055,179	04/25/00	Koganei et al.			
DJ		6,107,653	08/22/00	Fitzgerald			
DK		6,113,690	09/05/00	Yu et al.			
DL		6,114,996	09/05/00	Nghiem			
DM		6,121,642	09/19/00	Newns			
DN		6,128,178	10/03/00	Newns			
DO		6,143,072	11/07/00	McKee et al.			
DP		6,184,144	02/06/01	Lo			
DQ		6,222,654	04/24/01	Frigo			

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EWB	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

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BNA	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KTB	JA	5,650,646	07/22/97	Summerfelt			
	JB	5,656,382	08/12/97	Nashimoto			
	JC	5,659,180	08/19/97	Shen et al.			
	JD	5,661,112	08/26/97	Hatta et al.			
	JE	5,679,965	11/95	Schetzina			
	JF	5,725,641	03/10/98	MacLeod			
	JG	5,745,631	04/28/98	Reinker			
	JH	5,776,621	07/07/98	Nashimoto			
	JI	5,777,350	07/07/98	Nakamura et al.			
	JJ	5,789,845	08/04/98	Wadaka et al.			
	JK	5,792,569	08/11/98	Sun et al.			
	JL	5,792,679	08/11/98	Nakato			
	JM	5,796,648	08/18/98	Kawakubo et al.			
	JN	5,801,072	09/01/98	Barber			
	JO	5,812,272	09/22/98	King et al.			
	JP	5,814,583	09/98	Itozaki et al.			
	Q	5,825,055	10/20/98	Summerfelt			
	Q	5,827,755	10/27/98	Yonchara et al.			
	Q	5,833,603	11/10/98	Kovacs et al.			
	Q	5,838,035	11/17/98	Ramesh			
Q	5,844,260	12/01/98	Ohori				
Q	5,846,846	12/08/98	Suh et al.				
Q	5,863,326	01/26/99	Nause et al.				
Q	5,872,493	02/16/99	Ella				
Q	5,879,956	03/99	Seon et al.				
Q	5,880,452	03/09/99	Plesko				
Q	5,883,564	03/16/99	Partin				
Q	5,907,792	05/25/99	Droopad et al.				
Q	5,937,274	08/10/99	Kondow et al.				
Q	5,948,161	09/07/99	Kizuki				
Q	5,959,879	09/28/99	Koo				
Q	5,966,323	10/99	Chen et al.				
Q	5,987,011	11/16/99	Toh				
Q	6,022,140	02/08/00	Fraden et al.				
Q	6,022,410	02/08/00	Yu et al.				
Q	6,023,082	02/08/00	McKee et al.				
Q	6,028,853	02/22/00	Haartsen				
Q	6,049,702	04/11/00	Tham et al.				
Q	6,078,717	06/20/00	Nashimoto et al				
Q	6,088,216	07/00	Laibowitz et al.				
Q	6,090,659	07/00	Laibowitz et al.				
Q	6,107,721	08/22/00	Lakin				
Q	6,153,010	11/28/00	Yyoku et al				

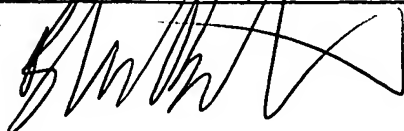
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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
B/M	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Aliman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				
LP	4,901,133	02/13/90	Curran et al.				
LQ	5,514,904	05/07/96	Onga et al.				

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BM	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	Kieg et al.			



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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>EWB</i>	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thomton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
OU	5,789,733	08/04/98	Jachimowicz et al.				
OV	5,753,300	05/19/98	Wessels et al.				
OW	6,208,453	03/27/01	Wessels et al.				
OX	5,886,867	03/23/99	Chivukula et al.				
OY	5,028,976	07/02/91	Ozaki et al.				
OZ	5,869,845	02/09/99	Vander Wagt et al.				
PA	5,596,214	01/21/97	Endo				
PB	6,391,674 B2	05/21/02	Ziegler				
PC	6,275,122 B1	08/14/01	Speidell et al.				
PD	6,238,946 B1	05/29/01	Ziegler				
PE	6,210,988 B1	04/03/01	Howe et al.				
PF	6,392,257	05/21/02	Ramdani et al.				
PG	4,442,590	04/17/84	Stockton et al.				
PH	5,603,764	02/18/97	Matsuda et al.				
PI	6,087,681	06/11/00	Shakuda				
PJ	5,132,648	07/21/92	Trinh et al.				
PK	6,427,066	07/30/02	Grube				
PL	2002/0072245	06/13/02	Ooms et al.				
PM	6,278,138 B1	08/21/01	Suzuki				
PN	5,888,296	03/30/99	Ooms et al.				
PO	5,198,269	03/30/93	Swartz et al.				
PP	2002/0030246	03/14/02	Eisenbeiser et al.				
PQ	2002/0071143	04/25/02	Ramdani et al.				

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
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EnB	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
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	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
QU	5,334,556	08/02/94	Guldi				
QV	4,910,164	03/20/90	Shichijo				
QW	4,952,420	08/28/90	Walters				
QX	6,121,647	09/19/00	Yano et al.				
QY	6,306,668 B1	10/23/01	McKee et al.				
QZ	6,143,366	11/07/00	Lu				
RA	6,410,941	06/25/02	Taylor et al.				
RB	5,397,428	03/14/95	Stoner et al.				
RC	6,432,546 B1	08/13/02	Ramesh et al.				
RD	6,345,424	02/12/02	Hasegawa et al.				
RE	6,338,756 B2	01/15/02	Dietze				
RF	5,516,725	05/14/96	Chang et al.				
RG	4,667,212	05/19/87	Nakamura				
RH	5,629,534	05/13/97	Inuzuka et al.				
RI	3,914,137	10/21/75	Huffman et al.				
RJ	5,753,928	05/19/98	Krause				
RK	5,977,567	11/02/99	Verdiell				
RL	5,130,762	07/14/92	Kulick				
RM	5,621,227	04/15/97	Joshi				
RN	6,389,209 B1	05/14/02	Suhr				
RO	5,163,118	11/10/92	Lorenzo et al.				
RP	5,926,493	07/20/99	O'Brien et al.				
RQ	5,323,023	06/21/94	Fork				

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BMB	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alfemess et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al.			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
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	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
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	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilyalli et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	02/15/00	Grigorian et al.			

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	UB	5,427,988	06/27/95	Sengupta et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
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	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
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	ABK	60-210018	10/22/85	Japan w/English Abstract			
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	ABM	0 682 266	11/15/95	Europe			
	ABN	3-41783	02/91	Japan (English Abstract only)			
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	BAE	WO 94/03908	02/17/94	WIPO			
	BAF	WO 01/33585	05/10/01	WIPO			
	BAG	1-102435	04/20/89	Japan w/English Abstract			
	BAH	52-135684	11/12/77	Japan (English Abstract)			
	BAI	02051220	02/21/90	Japan (English Abstract)			
	BAJ	11135614	05/21/99	Japan (w/English Abstract)			
	BAK	64-52329	02/28/89	Japan (w/English Abstract)			
	BAL	10-256154	09/25/98	Japan (w/English Abstract)			
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	BAZ	9-67193	03/11/97	Japan w/English Abstract			
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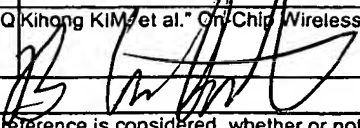
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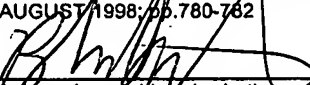
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b/wb	CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.					
	CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.					
	CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 <i>Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.					
	CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.					
	CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO ₃ Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.					
	CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.					
	CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," 1997 <i>Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.					
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	CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.					
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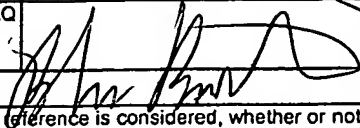
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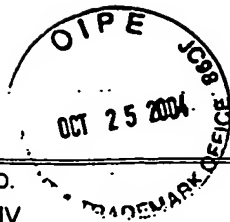
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BWB	JJAA	A.J. Moulson et al.; "Electroceramics Materials Properties Applications"; Chapman & Hall; pp. 366-369					
	JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114					
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	JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322					
	JJAE	A.Y. Wu et al.; "Highly Oriented (Pb,Lu)(Zr,Ti)O ₃ Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304					
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	KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907					
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	KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225					
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	KKAO						
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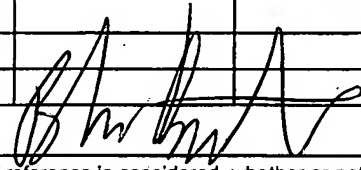
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	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			

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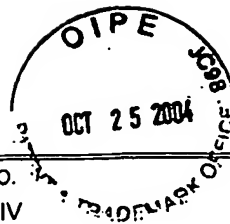
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	VW	2002/0079576	Seshan			 <div style="font-size: 4em; transform: rotate(45deg); display: inline-block;">/</div> 		
	VX	5,148,504	09/15/92	Levi et al.				
	VY	2002/0195610 A1	12/26/02	Klosowiak				
	VZ	5,477,363	12/19/95	Matsuda				
	WA	5,905,571	05/18/99	Butler et al.				
	WB	5,570,226	10/29/96	Ota				
	WC	5,087,829	02/11/92	Ishibashi et al.				
	WD	2001/0020278 A1	09/06/01	Saito				
	WE	6,496,469 B1	12/17/02	Uchizaki				
	WF	5,679,947	10/21/97	Doi et al.				
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.				
	WH	5,446,719	08/29/95	Yoshida et al.				
	WI	5,831,960	11/03/98	Jiang et al.				
	WJ	5,693,140	12/02/97	McKee et al.				
	WK	6,376,337 B1	04/23/02	Wang et al.				
	WL	4,177,094	12/04/79	Kroon				
	WM	5,216,359	06/01/93	Makki et al.				
	WN	6,307,996 B1	10/23/01	Nashimoto et al.				
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WT	5,959,308	09/28/99	Shichijo et al.					
WU	5,362,972	11/08/94	Yazawa et al.					
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WX	5,937,115	08/10/99	Domash					
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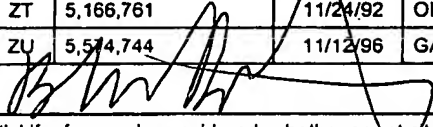
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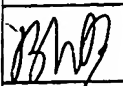
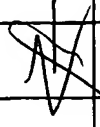
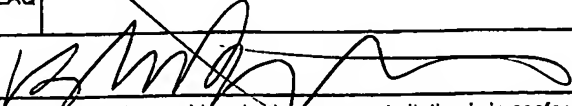
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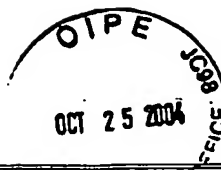
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	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
	ZS	6,051,874	04/18/00	MASUDA			
	ZT	5,166,761	11/24/92	OLSON ET AL			
ZU	5,574,744	11/12/96	GAW ET AL				
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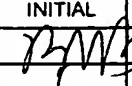
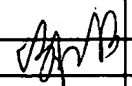
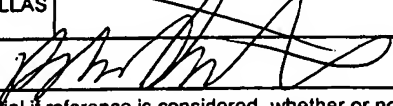
Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248402US99DIV		SERIAL NO. 10/767,994	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
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BMP	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT			
	CCB	2 152 315	07/31/85	GREAT BRITAIN			
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT			
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)			
	CCE	WO 03/012874	02/13/03	WIPO			
	CCF	1 043 427	10/11/00	EUROPE			
	CCG	1 069 605	01/17/01	EUROPE			
	CCH	WO 02/099885	12/12/02	WIPO			
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT			
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)			
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)			
	CCL	WO 02/11254	02/07/02	WIPO			
	CCM	0 494 514	07/15/92	EUROPE			
	CCN	0 247 722	12/02/87	EUROPE			
	CCO	1 037 272	09/20/00	EUROPE			
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)			
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT			
CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT				
CCS	0 392 714	10/17/90	EUROPE				
	CCT						
	CCU						
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				OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3					
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001					
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3					
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3					
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO3 Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651					
	LLAF	V. Bormand et al.; "Deposition of LiTaO3 thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244					
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296					
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr0.52Ti0.48)O3 epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460					
	LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US					
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	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287					
	LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958					
	LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246					
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO3 at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169					
	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536					
	LLAP						
	LLAQ						
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				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	ZV	5,122,679	06/16/92	ISHII ET AL			
	ZW	6,232,806	05/15/01	WOESTE ET AL			
	ZX	5,430,397	07/04/95	ITOH ET AL			
	ZY	6,151,240	11/21/00	SUZUKI			
	ZZ	6,528,374	03/04/03	BOJARCZUK, JR ET AL			
	A1	6,589,887	07/08/03	DALTON ET AL			
	A2	5,064,781	11/12/91	CAMBOU ET AL			
	A3	2002/0052061	05/02/02	FITZGERALD			
	A4	5,696,392	12/09/97	CHAR ET AL			
	A5	5,986,301	11/16/99	FUKUSHIMA ET AL			
	A6	6,329,277	12/11/01	LIU ET AL			
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	A8						
	A9						
FOREIGN PATENT DOCUMENTS							
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	CCT	WO 95/02904	01/26/95	WIPO			
	CCU	WO 02/009150	01/31/02	WIPO			
	CCV	0 766 292	04/02/97	EUROPE			
	CCW	198 29 609	01/05/00	GERMANY			
	CCX	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
	CCZ	1 176 230	01/30/02	EUROPE			
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	LLAP	YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405					
	LLAQ	XIAMING HU et al; "Sr/Si template formation for the epitaxial growth of SrTiO/sub 3/on silicon" Materials Research Society Proceedings, Vol. 716, 2002, pp. 261-266					
	LLAR						
	LLAS						<input type="checkbox"/> Additional References sheet(s) attached
Examiner 					Date Considered 1/2/05		

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